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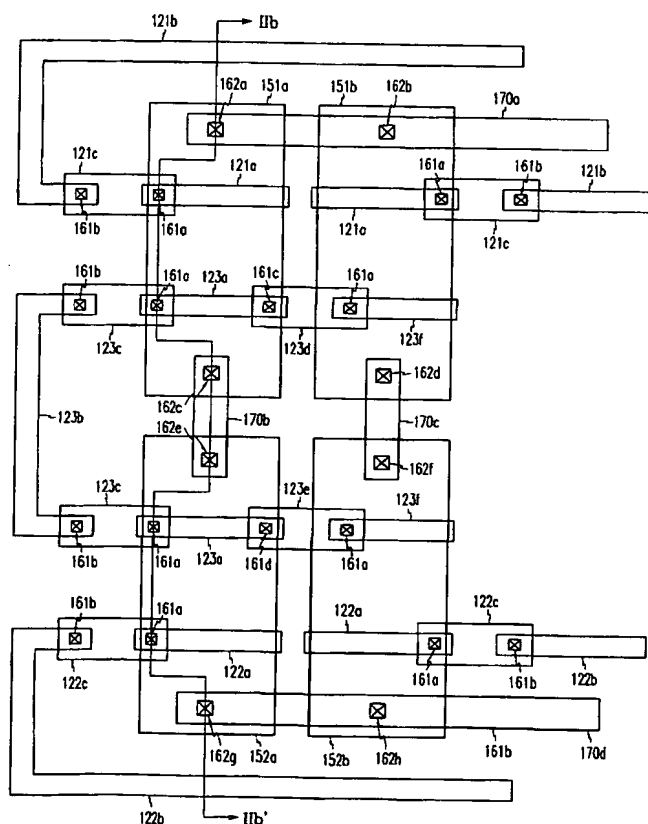
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(54) Title: THIN FILM TRANSISTOR ARRAY PANEL AND MANUFACTURING METHOD THEREOF



(57) Abstract: A thin film transistor array panel includes: an insulating substrate (110); first and second semiconductor members (151 a,b) formed on the substrate and having opposite conductivity; a first gate member (121a) insulated from the first and the second semiconductor members and overlapping one of the first and the second semiconductor members; a second gate member (122a) formed on the same layer as the first gate member (121a), separated from the first gate member, and insulated from the first and the second semiconductor members (151 a,b), the second gate member (122a) not overlapping the first and the second semiconductor members; a first data member (162) connected to one of the first and the second semiconductor members (151 a,b) and insulated from the first (121a) and the second (122a) gate members; and a first connection (123) formed on the same layer as the first data member and connecting the first gate member (121a) and the second gate member (122a).

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